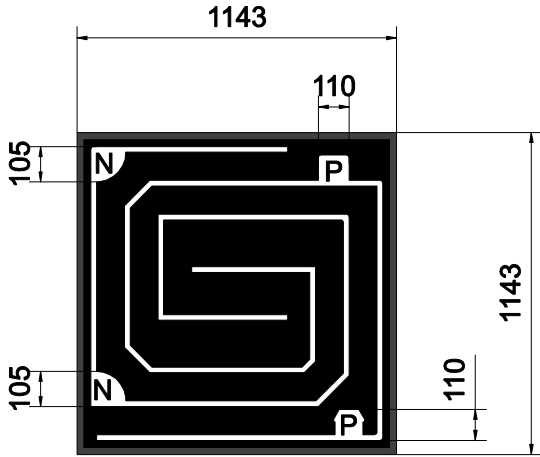


Radiation	Type	Technology	Electrodes
Blue		InGaN/Al ₂ O ₃	Both on top side

	typ. dimensions (μm)
	<p>typ. thickness 100 (±10) μm</p> <p>p and n contact gold alloy</p> <p>backside metalization gold alloy</p>

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		2.7	3.1	V
Forward voltage ²	I _F = 350 mA	V _F		3.5		V
Reverse voltage	I _R = 10 μA	V _R	5V			V
Radiant power ¹	I _F = 20 mA	Φ _e	14	18		mW
Radiant power ¹	I _F = 350 mA	Φ _e	200	250		mW
Luminous intensity ¹	I _F = 350 mA	I _v	1500	2500		mcd
Peak wavelength	I _F = 350 mA	λ _P	445	455	465	nm
Dominant wavelength	I _F = 350 mA	λ _D	455	465	475	nm
Spectral bandwidth at 50%	I _F = 20 mA	Δλ _{0.5}		25		nm
Switching time	I _F = 20 mA	t _r , t _f		50		ns

¹Measured on bare chip with EPIGAP equipment

Labeling

Type	Lot N°	I _v (typ) [mcd]	V _F (typ) [V]	Quantity
ELC-460-31-2				

Packing: Chips on adhesive film with wire-bond side on top

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each application by the customers themselves.

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